-100mA / -50V Digital transistors (with built-in resistors)

DTA114TM / DTA114TE / DTA114TUA DTA114TKA / DTA114TSA

Applications

Inverter, Interface, Driver

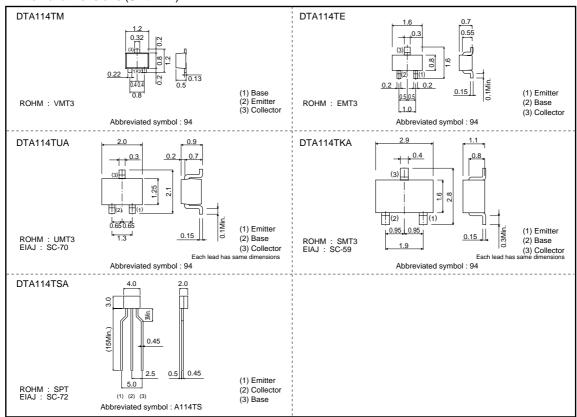
Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making the device design easy.

Structure

PNP epitaxial planar silicon transistor (Resistor built-in type)

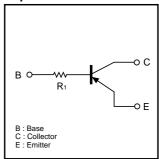
●External dimensions (Unit: mm)



Packaging specifications

	Package	VMT3	EMT3	UMT3	SMT3	SPT
Package type		Taping	Taping	Taping	Taping	Taping
	Code	T2L	TL	T106	T146	TP
Part No.	Basic ordering unit (pieces)	8000	3000	3000	3000	5000
DTA114TM		0	-	-	-	_
DTA114TE		-	0	-	-	-
DTA114TUA	4	-	-	0	-	-
DTA114TKA		-	-	-	0	_
DTA114TSA		-	-	-	-	0

●Equivalent circuit



R1=10kΩ

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits					
		DTA114TM	DTA114TE	DTA114TUA	DTA114TKA	DTA114TSA	Unit
Collector-base voltage	Vсво	-50				V	
Collector-emitter voltage	VCEO	-50					V
Emitter-base voltage	VEBO		V				
Collector current	lc	-100					mA
Collector power dissipation	Pc	1:	50	20	00	300	mW
Junction temperature	Tj	150					°C
Storage temperature	Tstg	−55 to +150					°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-50	-	-	V	Ic=-50μA
Collector-emitter breakdown voltage	BVceo	-50	-	-	V	Ic=-1mA
Emitter-base breakdown voltage	ВУЕВО	-5	-	-	V	IE=-50μA
Collector cutoff current	Ісво	-	-	-0.5	μΑ	Vcb=-50V
Emitter cutoff current	ІЕВО	_	_	-0.5	μΑ	VEB=-4V
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.3	V	Ic/Iв=-10mA/-1mA
DC current transfer ratio	hFE	100	250	600	-	Vce=-5V, Ic=-1mA
Input resistance	R1	7	10	13	kΩ	_
Transition frequency	f⊤ *	-	250	-	MHz	VcE=-10V, IE=5mA, f=100MHz

^{*} Characteristics of built-in transistor

•Electrical characteristic curves

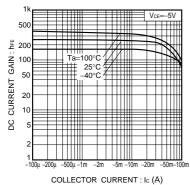


Fig.1 DC current gain vs. collector current

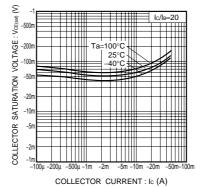


Fig.2 Collector-emitter saturation voltage vs. collector current

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